FEATURES

■ Avalanche Rugged Technology

■ Rugged Gate Oxide Technology

■ Lower Input Capacitance

■ Improved Gate Charge

■ Extended Safe Operating Area

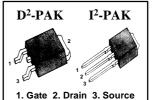
■ Lower Leakage Current : $10 \mu A (Max.)$ @ $V_{DS} = -200 V$

■ Low $R_{DS(ON)}$: 2.084 Ω (Typ.)

 $BV_{DSS} = -200 V$

 $R_{DS(on)} = 3.0 \Omega$

 $I_D = -1.75 A$



Absolute Maximum Ratings

Symbol	Characteristic	Value	Units	
V_{DSS}	Drain-to-Source Voltage	-200	V	
	Continuous Drain Current (T _C =25°C)	-1.75		
I _D	Continuous Drain Current (T _C =100°C)	-1.0	Α	
I _{DM}	Drain Current-Pulsed	-7.0	Α	
V _{GS}	Gate-to-Source Voltage	<u>+</u> 30	V	
E _{AS}	Single Pulsed Avalanche Energy 2	143	mJ	
I _{AR}	Avalanche Current ①	-1.75	Α	
E _{AR}	Repetitive Avalanche Energy ①	2.0	mJ	
dv/dt	Peak Diode Recovery dv/dt 3	-5.0	V/ns	
	Total Power Dissipation (T _A =25°C) *	3.1	W	
P _D	Total Power Dissipation (T _C =25°C)	20	W	
	Linear Derating Factor	0.16	W/°C	
T_J , T_STG	Operating Junction and	FF to 1150		
'J,'STG	Storage Temperature Range	- 55 to +150	0.0	
T _L	Maximum Lead Temp. for Soldering	300	°C	
' L	Purposes, 1/8" from case for 5-seconds	300		

Thermal Resistance

Symbol	Characteristic	Тур.	Max.	Units	
$R_{\theta JC}$	Junction-to-Case		6.25		
$R_{\scriptscriptstyle{ hetaJA}}$	Junction-to-Ambient *		40	°C/W	
$R_{\theta JA}$	Junction-to-Ambient		62.5		

^{*} When mounted on the minimum pad size recommended (PCB Mount).



Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition
BV _{DSS}	Drain-Source Breakdown Voltage	-200	1		V	$V_{GS} = 0V, I_{D} = -250 \mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.		-0.2		V/°C	I _D =-250μA See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	-2.0		-4.0	V	V_{DS} =-5V, I_{D} =-250 μ A
	Gate-Source Leakage, Forward			-100	nA	V _{GS} =-30V
I _{GSS}	Gate-Source Leakage, Reverse			100	ПА	V _{GS} =30V
١,	Drain to Course Lackage Current			-10	μΑ	V _{DS} =-200V
I _{DSS}	Drain-to-Source Leakage Current			-100		V _{DS} =-160V,T _C =125°C
R _{DS(on)}	Static Drain-Source On-State Resistance			3.0	Ω	V _{GS} =-10V,I _D =-0.9A ④
g_{fs}	Forward Transconductance		1.1		Ω	V_{DS} =-40V, I_{D} =-0.9A 4
C _{iss}	Input Capacitance		220	285		\/ _0\/\/ _ 25\/f_1MUz
C _{oss}	Output Capacitance		45	65	pF	V_{GS} =0V, V_{DS} =-25V,f =1MHz
C _{rss}	Reverse Transfer Capacitance		16	25		See Fig 5
t _{d(on)}	Turn-On Delay Time		10	30		V _{DD} =-100V,I _D =-1.75A,
t _r	Rise Time		20	50	ns	$R_{G}=18 \Omega$
t _{d(off)}	Turn-Off Delay Time		27	65	115	
t _f	Fall Time		12	35		See Fig 13 ④⑤
Q_g	Total Gate Charge		9	11		V _{DS} =-160V,V _{GS} =-10V,
Q_{gs}	Gate-Source Charge		1.8		nC	I _D =-1.75A
Q_{gd}	Gate-Drain("Miller ") Charge		4.8			See Fig 6 & Fig 12 ④⑤

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic		Min.	Тур.	Max.	Units	Test Condition
I _S	Continuous Source Current			-	-1.75		Integral reverse pn-diode
I _{SM}	Pulsed-Source Current	0		1	-7.0	Α	in the MOSFET
V _{SD}	Diode Forward Voltage	4		-	-4.0	V	T _J =25°C,I _S =-1.75A,V _{GS} =0V
t _{rr}	Reverse Recovery Time			110		ns	T _J =25°C,I _F =-1.75A
Q _{rr}	Reverse Recovery Charge			0.42		μС	di _F /dt=100A/μs ④

- Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- ② L=70mH, I_{AS} =-1.75A, V_{DD} =-50V, R_{G} =27 Ω^* , Starting T_J =25°C ③ I_{SD} ≤-1.75A, di/dt ≤ 250A/ μ s, V_{DD} ≤B V_{DSS} , Starting T_J =25°C ④ Pulse Test : Pulse Width = 250 μ s, Duty Cycle ≤ 2%

- **5** Essentially Independent of Operating Temperature



Fig 1. Output Characteristics

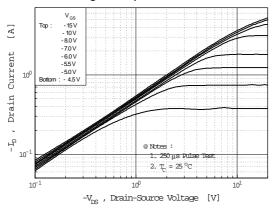


Fig 2. Transfer Characteristics

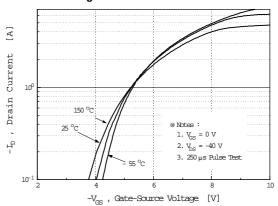


Fig 3. On-Resistance vs. Drain Current

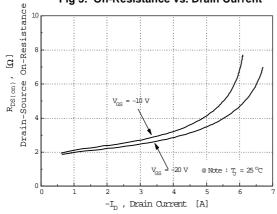


Fig 4. Source-Drain Diode Forward Voltage

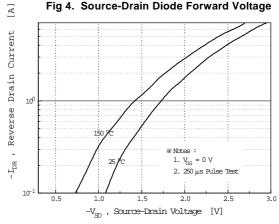


Fig 5. Capacitance vs. Drain-Source Voltage

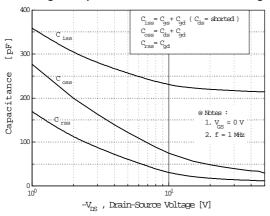
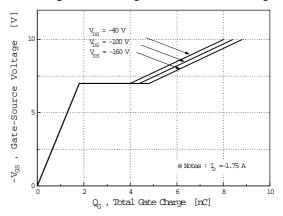
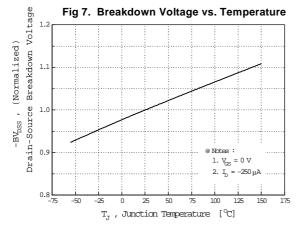
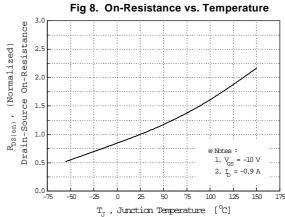


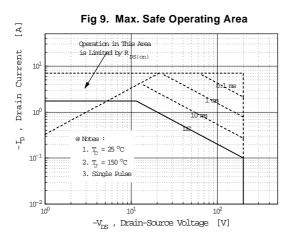
Fig 6. Gate Charge vs. Gate-Source Voltage

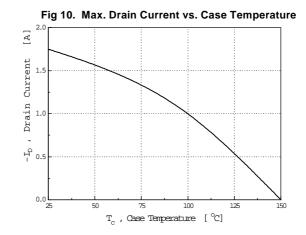












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Fig 11. Thermal Response



Fig 12. Gate Charge Test Circuit & Waveform

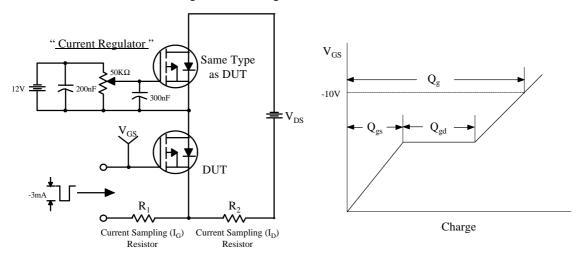


Fig 13. Resistive Switching Test Circuit & Waveforms

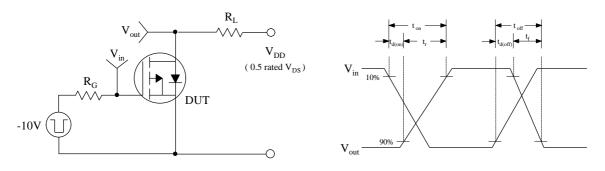


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

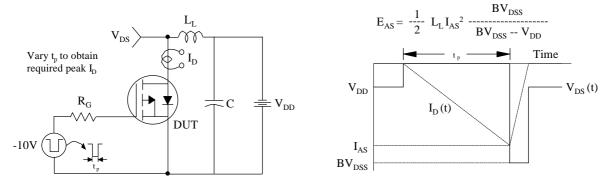
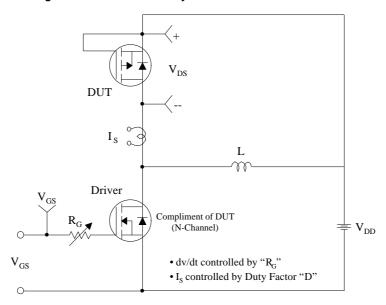
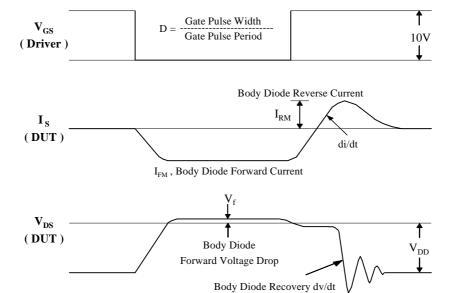




Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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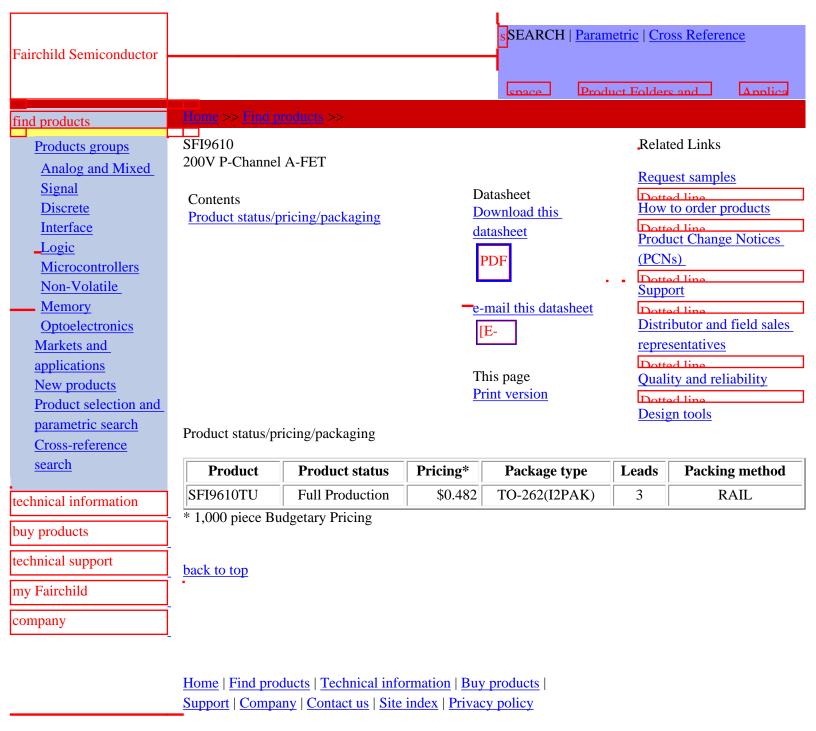
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